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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 20030027395 A1	20030206	15	Method of fabricating a DRAM semiconductor device	438/305	438/231; 438/232;
2	☐	☐	US 20030008469 A1	20030109	28	DRAM cell capacitor and manufacturing method thereof	438/396	438/253
3	☐	☐	US 20020167036 A1	20021114	20	Method for fabricating DRAM cell and DRAM cell	257/296	
4	☐	☐	US 20020160550 A1	20021031	11	Semiconductor device including storage nodes of	438/60	
5	☐	☐	US 20020113273 A1	20020822	6	Semiconductor device having contact plug and method for	257/374	
6	☐	☐	US 20010055842 A1	20011227	29	Methods of forming self-aligned contact pads	438/183	438/184; 438/230;
7	☐	☐	US 20010006242 A1	20010705	10	Semiconductor device with pillar-shaped capacitor	257/311	257/306; 438/253;
8	☐	☐	US 6548853 B1	20030415	15	Cylindrical capacitors having a stepped sidewall	257/306	257/307; 257/308;
9	☐	☐	US 6534813 B1	20030318	29	Semiconductor device having a self-aligned contact	257/300	438/396
10	☐	☐	US 6518671 B1	20030211	14	Bit line landing pad and borderless contact on bit	257/758	257/760; 438/639
11	☐	☐	US 6489195 B1	20021203	19	Method for fabricating DRAM cell using a protection	438/238	438/396

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Document Listing

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US006225167	13	1 - 13	1
US005779520	13	1 - 13	1
US005767004	9	1 - 9	1
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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☑	US 20020058408 A1	20020516	17	Method and apparatus for forming metal interconnects	438/637	
2	☐	☑	US 6383917 B1	20020507	9	Method for making integrated circuits	438/637	438/304; 438/305;
3	☑	☑	US 6380084 B1	20020430	21	Method to form high performance copper damascene	438/687	438/622; 438/637;
4	☐	☑	US 6221754 B1	20010424	7	Method of fabricating a plug	438/619	438/421; 438/422;
5	☑	☑	US 6114243 A	20000905	15	Method to avoid copper contamination on the	438/687	438/633; 438/638;
6	☐	☑	US 6114238 A	20000905	5	Self-aligned metal nitride for copper passivation	438/648	438/659; 438/687;
7	☐	☑	US 6046108 A	20000404	9	Method for selective growth of Cu.sub.3 Ge or Cu.sub.5	438/687	438/626; 438/627;
8	☐	☑	US 6043148 A	20000328	10	Method of fabricating contact plug	438/628	438/643; 438/644;
9	☐	☑	US 5985751 A	19991116	16	Process for fabricating interconnection of	438/637	438/632; 438/634;
10	☐	☑	US 5972786 A	19991026	9	Contact hole structure in a semiconductor and formation	438/627	438/629; 438/632;
11	☐	☑	US 5895268 A	19990420	7	High pressure nitridation of tungsten	438/672	438/637; 438/675;

§ 1.121(c) - Amendment by Replacement Claims

How to make amendments to the claims (cont.):

- A claim may be canceled by an instruction (e.g., "cancel claim 3")

- A canceled claim can be reinstated only by re-presentation of the complete text of the claim with a new claim number

- The clean version will be printed in the patent; applicant must provide accurate version; examiner must ensure patentability of clean version

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FORMAT SLIDE
Recommended Format for Submitting Amendments with Replacement Paragraphs/Sections/Claims

- The following **FORMAT** is recommended for the amendment portion of the amendment paper:
  - First: A clean version of each replacement paragraph/section/claim along with clear instructions for entry
  - Second: Starting on a separate page, all appropriate remarks/arguments, 37 CFR 1.111 and MPEP 714
  - Third: starting on a separate page, a marked-up version entitled: **"Version with markings to show changes made"**

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
6	☐	☑	US 6114238 A	20000905	5	Self-aligned metal nitride for copper passivation	438/648	438/659; 438/687;
7	☐	☑	US 6046108 A	20000404	9	Method for selective growth of Cu.sub.3 Ge or Cu.sub.5	438/687	438/626; 438/627;
8	☐	☑	US 6043148 A	20000328	10	Method of fabricating contact plug	438/628	438/643; 438/644;
9	☐	☑	US 5985751 A	19991116	16	Process for fabricating interconnection of	438/637	438/632; 438/634;
10	☐	☑	US 5972786 A	19991026	9	Contact hole structure in a semiconductor and formation	438/627	438/629; 438/632;
11	☐	☑	US 5895268 A	19990420	7	High pressure nitridation of tungsten	438/672	438/637; 438/675;
12	☐	☑	US 5527739 A	19960618	9	Process for fabricating a semiconductor device having	438/627	438/629; 438/648;
13	☑	☑	US 5527736 A	19960618	6	Dimple-free tungsten etching back process	438/648	438/672; 438/976
14	☐	☑	US 5470789 A	19951128	18	Process for fabricating integrated circuit devices	438/643	438/648; 438/675;
15	☐	☑	US 5422310 A	19950606	9	Method of forming interconnection in	438/648	216/13; 216/58;

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§ 1.121(c) - Amendment by Replacement Claims

How to make amendments to the claims:

- Submit a clean (with no underlining and bracketing) amended claim as the official version with an instruction to substitute it for the pending claim with the same number; also submit a marked-up version of the prior pending claim with all changes shown by any conventional comparison system as an aid to the examiner

- Any new or canceled claim does not have to be in marked-up version; an indication that claim X is new or claim Y was canceled is sufficient

- Both the clean amended claim and the marked-up version should have the same expression: "amended," "twice amended," etc., in parentheses after claim number

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§1.121(c)(3) - Amendment by Replacement Claims

How to make amendments to the claims (cont.):

- OPTIONAL: A clean set of all pending claims with the same numbers as the pending claims being re-presented can be submitted at any time (provided the requirements of §§ 1.116 and 1.312 are met)

- This submission will be entered as the official version and will be construed as directing the cancellation of all previous versions of the re-presented claims

- The absence of an accompanying marked up version constitutes an assertion that the claim has not been changed relative to the immediate prior version

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